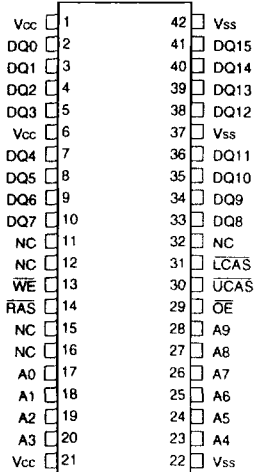




1Mx16 CMOS FPM Dynamic RAM

PRELIMINARY*

PIN CONFIGURATION TOP VIEW



PIN DESCRIPTION

A0-9	Address Inputs
DQ0-15	Data Input/Outputs
\overline{OE}	Output Enable
\overline{WE}	Write Enable
\overline{RAS}	Row Address Strobe
UCAS	Upper Column Address Strobe
LCAS	Lower Column Address Strobe
Vcc	+5.0V Power Supply
Vss	Ground
NC	Not Connected

PLASTIC PLUS™ FEATURES

- Fast Access Time (t_{RAC}): 70, 80, 100ns
- Power Supply: 5V \pm 0.5V
- Packaging
 - 42 Lead Plastic Surface-Mount SOJ (TJ)
- Commercial, Industrial and Military Temperature Ranges
- Three-State Unlatched Output
- Fast Page Mode
- TTL-Compatible Inputs and Outputs
- \overline{RAS} -Only Refresh
- xCAS Before \overline{RAS} Refresh
- Hidden Refresh
- 1024 Cycle Refresh in 16ms
- Low Power Dissipation
- Long Refresh Period Option

* This data sheet describes a product under development, not fully characterized, and is subject to change without notice.





OPERATIONS

DUAL $\overline{\text{CAS}}$

Two $\overline{\text{CAS}}$ pins ($\overline{\text{LCAS}}$ and $\overline{\text{UCAS}}$) are provided to give independent control of the 16 data-I/O pins (DQ0-15), with $\overline{\text{LCAS}}$ corresponding to DQ0-7 and $\overline{\text{UCAS}}$ corresponding to DQ8-15. For read or write cycles, the column address is latched on the first $\overline{\text{xCAS}}$ falling edge. Each $\overline{\text{xCAS}}$ going low enables its corresponding DQx pin with data associated with the column address latched on the first falling $\overline{\text{xCAS}}$ edge. All address setup and hold parameters are referenced to the first falling $\overline{\text{xCAS}}$ edge. The delay time from $\overline{\text{xCAS}}$ low to valid data out (see parameter t_{CAC}) is measured from each individual $\overline{\text{xCAS}}$ to its corresponding DQx pin.

In order to latch in a new column address, both $\overline{\text{xCAS}}$ pins must be brought high. The column-precharge time (see parameter t_{CP}) is measured from the last $\overline{\text{xCAS}}$ rising edge to the first $\overline{\text{xCAS}}$ falling edge of the new cycle. Keeping a column address valid while toggling $\overline{\text{xCAS}}$ requires a minimum setup time, t_{CLCH} . During t_{CLCH} , at least one $\overline{\text{xCAS}}$ must be brought low before the other $\overline{\text{xCAS}}$ is taken high.

For early-write cycles, the data is latched on the first $\overline{\text{xCAS}}$ falling edge. Only the DQs that have the corresponding $\overline{\text{xCAS}}$ low are written into. Each $\overline{\text{xCAS}}$ must meet t_{CAS} minimum in order to ensure writing into the storage cell. To latch a new address and new data, all $\overline{\text{xCAS}}$ pins must be high and meet t_{CP} .

PAGE MODE

Page-mode operation allows faster memory access by keeping the same row address while selecting random column addresses. The time for row-address setup and hold and address multiplex is eliminated. The maximum number of columns that can be accessed is determined by the maximum $\overline{\text{RAS}}$ low time and the $\overline{\text{xCAS}}$ page-mode cycle time used. With minimum $\overline{\text{xCAS}}$ page-cycle time, all columns can be accessed without intervening $\overline{\text{RAS}}$ cycles.

Unlike conventional page-mode DRAMs, the column address buffers in this device are activated on the falling edge of $\overline{\text{RAS}}$. The buffers act as transparent or flow-through latches while $\overline{\text{xCAS}}$ is high. The falling edge of the first $\overline{\text{xCAS}}$ latches the column addresses. This feature allows the devices to operate at a higher data bandwidth than conventional page-mode parts because data retrieval begins as soon as the column address is valid rather than when $\overline{\text{xCAS}}$ transitions low. This performance improvement is referred to as enhanced page mode. A valid column address may be presented immediately after t_{RAH} (row-address hold time) has

been satisfied, usually well in advance of the falling edge of $\overline{\text{xCAS}}$. In this case, data is obtained after t_{CAC} maximum (access time from $\overline{\text{xCAS}}$ low) if t_{AA} maximum (access time from column address) has been satisfied. In the event that column addresses for the next page cycle are valid at the time $\overline{\text{xCAS}}$ goes high, minimum access time for the next cycle is determined by t_{CPA} (access time from rising edge of the last $\overline{\text{xCAS}}$).

ADDRESS: A0-9

Twenty address bits are required to decode 1 of 1048576 storage cell locations. For the WPD1M16-XTJX, 10 row-address bits are set up on A0 through A9 and latched onto the chip by $\overline{\text{RAS}}$. Ten, column-address bits are set up on A0 through A9 and latched onto the chip by the first $\overline{\text{xCAS}}$. All addresses must be stable on or before the falling edge of $\overline{\text{RAS}}$ and $\overline{\text{xCAS}}$. $\overline{\text{RAS}}$ is similar to a chip enable in that it activates the sense amplifiers as well as the row decoder. $\overline{\text{xCAS}}$ is used as a chip select, activating its corresponding output buffer and latching the address bits into the column-address buffers.

WRITE ENABLE ($\overline{\text{WE}}$)

The read or write mode is selected through $\overline{\text{WE}}$. A logic high on $\overline{\text{WE}}$ selects the read mode and a logic low selects the write mode. The data inputs are disabled when the read mode is selected. When $\overline{\text{WE}}$ goes low prior to $\overline{\text{xCAS}}$ (early write), data out remains in the high-impedance state for the entire cycle, permitting a write operation with $\overline{\text{OE}}$ grounded.

DATA IN (DQ0-15)

Data is written during a write or read-modify-write cycle. Depending on the mode of operation, the falling edge of $\overline{\text{xCAS}}$ or $\overline{\text{WE}}$ strobes data into the on-chip data latch. In an early-write cycle, $\overline{\text{WE}}$ is brought low prior to $\overline{\text{xCAS}}$ and the data is strobed in by the first occurring $\overline{\text{xCAS}}$ with setup and hold times referenced to this signal. In a delayed-write or read-modify-write cycle, $\overline{\text{xCAS}}$ is already low and the data is strobed in by $\overline{\text{WE}}$ with setup and hold times referenced to this signal. In a delayed-write or read-modify-write cycle, $\overline{\text{OE}}$ must be high to bring the output buffers to the high-impedance state prior to impressing data on the I/O lines.

DATA OUT (DQ0-15)

Data out is the same polarity as data in. The output is in the high-impedance (floating) state until $\overline{\text{xCAS}}$ and $\overline{\text{OE}}$ are brought low. In a read cycle, the output becomes valid after the access time interval t_{CAC} (which begins with the negative transition of $\overline{\text{xCAS}}$) as long as t_{RAC} and t_{AA} are satisfied.



OUTPUT ENABLE (\overline{OE})

\overline{OE} controls the impedance of the output buffers. When \overline{OE} is high, the buffers remain in the high-impedance state. Bringing \overline{OE} low during a normal cycle activates the output buffers, putting them in the low-impedance state. It is necessary for both \overline{RAS} and \overline{xCAS} to be brought low for the output buffers to go into the low-impedance state, and they remain in the low-impedance state until either \overline{OE} or \overline{xCAS} is brought high.

RAS-ONLY REFRESH

A refresh operation must be performed at least once every 16 ms (128 ms for long refresh periods) to retain data. This can be achieved by strobing each of the 1024 rows (A0-9). A normal read or write cycle refreshes all bits in each row that is selected. A RAS-only operation can be used by holding both \overline{xCAS} at the high (inactive) level, conserving power as the output buffers remain in the high-impedance state. Externally generated addresses must be used for a \overline{RAS} -only refresh.

HIDDEN REFRESH

Hidden refresh can be performed while maintaining valid data at the output pin. This is accomplished by holding \overline{xCAS} at V_{IL} after a read operation and cycling \overline{RAS} after a specified precharge period, similar to a \overline{RAS} -only refresh cycle. The external address is ignored and the refresh address is generated internally.

\overline{xCAS} -BEFORE- \overline{RAS} (\overline{xCBB}) REFRESH

\overline{xCBB} refresh is utilized by bringing at least one \overline{xCAS} low earlier than \overline{RAS} (see parameter t_{CSR}) and holding it low after \overline{RAS} fails (see parameter t_{CHR}). For successive \overline{xCBB} refresh cycles, \overline{xCAS} can remain low while cycling \overline{RAS} . The external address is ignored and the refresh address is generated internally.

POWER UP

To achieve proper device operation, an initial pause of 200 μ s followed by a minimum of eight initialization cycles is required after power up to full V_{CC} level. These eight initialization cycles must include at least one refresh (\overline{RAS} -only or \overline{xCBB}) cycle.



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Min	Max	Unit
Operating Temperature	T _A	-55	+125	°C
Storage Temperature	T _{STG}	-65	+150	°C
Short Circuit Output Current	I _{OS}		50	mA
Power Dissipation	P _T		1	W
Supply Voltage Range	V _{CC}	-1.0	7.0	V
Voltage Range on any Pin*	V _T	-1.0	7.0	V

Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

* All voltage values are with respect to V_{SS}.

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V _{CC}	4.5	5.5	V
Input High Voltage	V _{IH}	2.4		V
Input Low Voltage*	V _{IL}		+0.8	V
Operating Temp. (Mil.)	T _A	-55	+125	°C
Operating Temp. (Ind.)	T _A	-40	+85	°C

* The algebraic convention, where the more negative (less positive) limit is designated as minimum, is used for logic-voltage levels only.

CAPACITANCE

(T_A = 25°C)

Parameter	Symbol	Max	Unit
A ₀₋₁₁ Input Capacitance	C _{I(A)}	10	pF
RAS and CAS Input Capacitance	C _{I(RC)}	10	pF
OE Input Capacitance	C _{I(OE)}	10	pF
WE Input Capacitance	C _{I(WE)}	10	pF
Output Capacitance	C _O	15	pF

This parameter is guaranteed by design but not tested.

DC CHARACTERISTICS

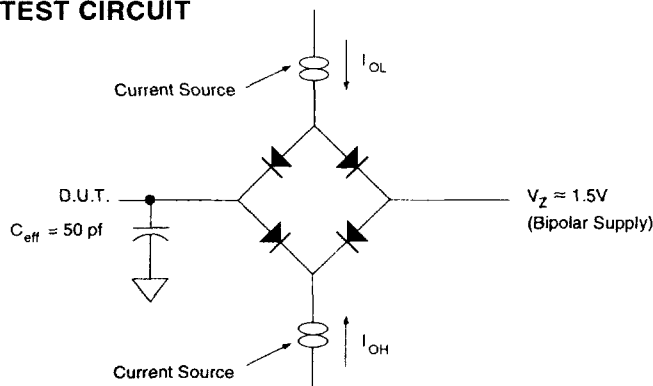
(V_{CC} = 5.0V, V_{SS} = 0V, T_A = -55°C to +125°C)

Parameter	Test Condition	Symbol	70		80		100		Units
			Min	Max	Min	Max	Min	Max	
High Level Output Voltage	I _{OH} = -5mA	V _{OH}	2.4		2.4		2.4		V
Low Level Output Voltage	I _{OL} = 4.2mA	V _{OL}		0.4		0.4		0.4	V
Input Current (Leakage)	V _I = 0V to +6.5V All others = 0V to V _{CC}	I _I		10		10		10	μA
output current (Leakage)	V _O = 0V to V _{CC} , CAS high	I _O		10		10		10	μA
Read or Write Cycle Current (1,2)	V _{CC} = 5.5V, minimum cycle	I _{CC1}		190		180		170	mA
Standby Current	V _{IH} = 2.4V (TTL), After 1 memory cycle, RAS and CAS high	I _{CC2}		2		2		2	mA
	V _{IH} = V _{CC} - 0.05V (CMOS), After 1 memory cycle, RAS and CAS high	I _{CC2}		1		1		1	mA
Average Page Current (2)	RAS low, CAS cycling	I _{CC4}		100		90		80	mA

NOTES:

1. Measured with a maximum of one address change while RAS = V_{IL}.
2. Measured with a maximum of one address change while CAS = V_{IH}.

AC TEST CIRCUIT



AC TEST CONDITIONS

Parameter	Typ	Unit
Input Pulse Levels	V _{IL} = 0, V _{IH} = 3.0	V
Input Rise and Fall	5	nS
Input and Output Reference Level	1.5	V
Output Timing Reference Level	1.5	V

NOTES:

V_Z is programmable from -2V to +7V.
I_{OL} & I_{OH} programmable from 0 to 16mA.
Tester Impedance Z₀ = 75 Ω.
V_Z is typically the midpoint of V_{OH} and V_{OL}.
I_{OL} & I_{OH} are adjusted to simulate a typical resistive load circuit.
ATE tester includes jig capacitance.

**AC CHARACTERISTICS***

(TA = -55°C to +125°C, VCC = 5.0V ±10%)

Parameter	Symbol	-70		-80		-100		Units
		Min	Max	Min	Max	Min	Max	
Column-Address Access Time	tAA		35		40		45	ns
CAS Low Access Time	tCAC		18		20		25	ns
Column Precharge Access Time	tCPA		40		45		50	ns
RAS Low Access Time	tRAC		70		80		100	ns
OE Low Access Time	tOEA		18		20		25	ns
Output Disable Time after CAS High (1)	tOFF	0	18	0	20	0	25	ns
Output Disable Time after OE High (1)	tOEZ	0	18	0	20	0	25	ns

* Valid data is presented at the outputs after all access times are satisfied but can go from the high-impedance state to an invalid-data state prior to the specified access times as the outputs are driven when CAS goes low.

1. toff and toez are specified when the outputs are no longer driven. The outputs are disabled by bringing either OE or CAS high.

AC CHARACTERISTICS

(VCC = 5.0V, VSS = 0V, TA = -55°C to +125°C)

Parameter	Symbol	-70		-80		-100		Units
		Min	Max	Min	Max	Min	Max	
Cycle Time, Read or Write Random (1)	trc	130		150		180		ns
Cycle Time, Read-Write (1)	trwc	181		205		245		ns
Cycle Time, Page Mode Read or Write (1,2)	tpc	45		50		55		ns
Cycle Time, Page Mode Read-Write (1)	tpwrc	96		105		120		ns
Pulse Duration, RAS Low Page Mode (3)	trasp	70	100,000	80	100,000	100	100,000	ns
Pulse Duration, RAS Low Nonpage Mode (3)	trasp	70	10,000	80	10,000	100	10,000	ns
Pulse Duration, CAS Low (4)	tcas	18	10,000	20	10,000	25	10,000	ns
Pulse Duration, CAS High	tcp	10		10		10		ns
Pulse Duration, RAS High (Precharge)	trp	50		60		70		ns
Pulse Duration, WE Low	twp	10		10		10		ns
Setup Time, Column Address before CAS Low	tasc	0		0		0		ns
Setup Time, Row Address before RAS Low	tasr	0		0		0		ns
Setup Time, Data (5)	tds	0		0		0		ns
Setup Time, WE High before CAS Low	trcs	0		0		0		ns
Setup Time, WE Low before CAS High	tcwl	18		20		25		ns
Setup Time, WE Low before RAS High	trwl	18		20		25		ns
Setup Time, WE Low before CAS Low (early-write operation only)	twcs	0		0		0		ns
Setup Time, WE High before RAS Low (CBR refresh only)	twrp	10		10		10		ns
Hold Time, Column Address after CAS Low	tcah	15		15		15		ns
Hold Time, Data (5)	tdh	15		15		15		ns
Hold Time, Row Address after RAS Low	trah	10		10		10		ns
Hold Time, WE High after CAS High (6)	trch	0		0		0		ns
Hold Time, WE High after RAS High (6)	trrh	0		0		5		ns

1. All cycle times assume tr = 5ns, reference to VIH (min) and VIL (max).

2. To assume tpc min, tasc should be ≥ tcp.

3. In read-write cycle, trwd and trwl must be observed.

4. In read-write cycle, tcwd and tcwl must be observed.

5. Referenced to the later of xCAS or WE in write operations.

6. Either trrh or trch must be satisfied for a read cycle.

**AC CHARACTERISTICS**(V_{CC} = 5.0V, V_{SS} = 0V, T_A = -55°C to +125°C)

Parameter	Symbol	-70		-80		-100		Units
		Min	Max	Min	Max	Min	Max	
\overline{WE} Low before \overline{CAS} Low Hold Time (early-write operation only)	t _{WCH}	15		15		15		ns
\overline{WE} High after \overline{RAS} Low Hold Time (CBR refresh only)	t _{WRH}	10		10		10		ns
\overline{OE} Command Hold Time	t _{OEH}	18		20		25		ns
\overline{RAS} Referenced to \overline{OE} Hold Time	t _{ROH}	10		10		10		ns
\overline{RAS} High from \overline{CAS} Precharge Hold Time	t _{RHCP}	40		45		50		ns
Column Address to \overline{WE} Low Delay Time (read-write operation only)	t _{AWD}	63		70		80		ns
\overline{RAS} Low to \overline{CAS} High Delay Time (CBR refresh only)	t _{CHR}	10		10		20		ns
\overline{CAS} High to \overline{RAS} Low Delay Time	t _{CRP}	5		5		5		ns
\overline{RAS} Low to \overline{CAS} High Delay Time	t _{CSH}	70		80		100		ns
\overline{CAS} Low to \overline{RAS} Low Delay Time (CBR refresh only)	t _{CSR}	5		5		10		ns
\overline{CAS} Low to \overline{WE} Low Delay Time (read-write operation only)	t _{CWD}	46		50		60		ns
\overline{OE} to Data Delay Time	t _{oED}	18		20		25		ns
\overline{RAS} Low to Column Address Delay Time (1)	t _{RAD}	15	35	15	40	15	55	ns
Column Address to \overline{RAS} High Delay Time	t _{RAL}	35		40		45		ns
Column Address to \overline{CAS} High Delay Time	t _{CAL}	35		40		45		ns
\overline{RAS} Low to \overline{CAS} Low Delay Time (1)	t _{RCD}	20	52	20	60	20	75	ns
\overline{RAS} High to \overline{CAS} Low Delay Time	t _{RPC}	0		0		0		ns
\overline{CAS} Low to \overline{RAS} High Delay Time	t _{RSH}	18		20		25		ns
\overline{RAS} Low to \overline{WE} Low Delay Time (read-write operation only)	t _{RWD}	98		110		135		ns
\overline{WE} Low after \overline{CAS} Precharge Delay Time (read-write operation only)	t _{CPW}	63		70		80		ns
Refresh Time Interval	t _{REF}		16		16		16	ms
Transition time (2)	t _T							

1. The maximum value is specified only to assure access time

2. Transition times (rise and fall) for \overline{RAS} and \overline{xCAS} are to be a minimum of 3ns and a maximum of 30ns.



ORDERING INFORMATION

W P D 1 M 16 X - X T J X

DEVICE GRADE:

- M = Military Temperature -55°C to +125°C
- I = Industrial Temperature -40°C to +85°C
- C = Commercial Temperature 0°C to +70°C

PACKAGE:

TJ = 42 Lead Plastic Surface Mount SOJ

ACCESS TIME in ns

IMPROVEMENT MARK

- B = Burn-in
- T = Temperature Cycle
- C = Burn-in and Temp Cycle

ORGANIZATION, 1M x 16

DRAM

PLASTIC PLUS™

WHITE MICROELECTRONICS